Driver Transistor

NPN Silicon

Features

- Moisture Sensitivity Level: 1
- ESD Rating:
 - ♦ Human Body Model 4 kV
 - ◆ Machine Model 400 V
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant*



Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	80	Vdc
Collector-Base Voltage	V _{CBO}	80	Vdc
Emitter-Base Voltage	V _{EBO}	4.0	Vdc
Collector Current – Continuous	Ι _C	500	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board $T_A = 25^{\circ}C$	P _D	460	mW
Thermal Resistance, Junction to Ambient (Note 1)	$R_{\theta JA}$	272	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-4 Board, 1 oz. Cu, 100 mm².

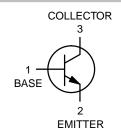


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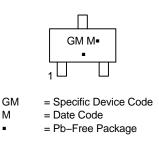
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SC-70 CASE 419 STYLE 3



MARKING DIAGRAM



(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBTA06WT1G	SC–70 (Pb–Free)	3,000 / Tape & Reel
SMMBTA06WT1G	SC–70 (Pb–Free)	3,000 / Tape & Reel
SMMBTA06WT3G	SC–70 (Pb–Free)	10,000 / Tape & Reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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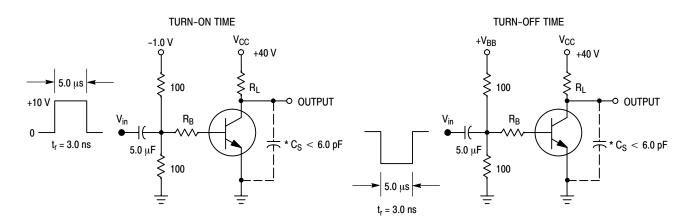
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS			•	•
Collector–Emitter Breakdown Voltage (Note 1) $(I_{C} = 1.0 \text{ mAdc}, I_{B} = 0)$	V _{(BR)CEO}	80	_	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100 \ \mu Adc, I_C = 0$)	V _{(BR)EBO}	4.0	_	Vdc
Collector Cutoff Current ($V_{CE} = 60 \text{ Vdc}, I_B = 0$)	ICES	_	0.1	μAdc
Collector Cutoff Current ($V_{CB} = 80 \text{ Vdc}, I_E = 0$)	Ісво	_	0.1	μAdc
ON CHARACTERISTICS				
DC Current Gain ($I_C = 10 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc}$) ($I_C = 100 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc}$)	h _{FE}	100 100		-
Collector–Emitter Saturation Voltage ($I_C = 100 \text{ mAdc}, I_B = 10 \text{ mAdc}$)	V _{CE(sat)}	_	0.25	Vdc
Base – Emitter On Voltage ($I_C = 100 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc}$)	V _{BE(on)}	_	1.2	Vdc

Current-Gain - Bandwidth Product (Note 2)	f _T			MHz
(I _C = 10 mA, V _{CE} = 2.0 V, f = 100 MHz)		100	-	

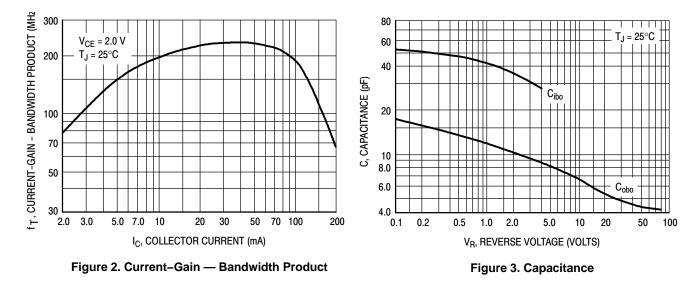
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2.0%. 2. f_T is defined as the frequency at which |h_{fe}| extrapolates to unity.



*Total Shunt Capacitance of Test Jig and Connectors For PNP Test Circuits, Reverse All Voltage Polarities

Figure 1. Switching Time Test Circuits



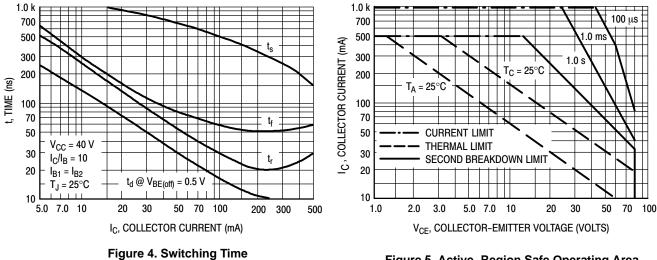
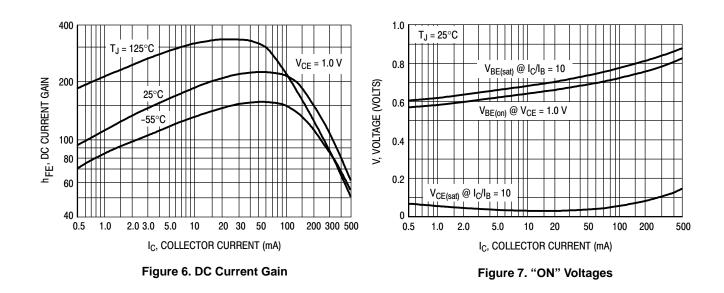


Figure 5. Active–Region Safe Operating Area



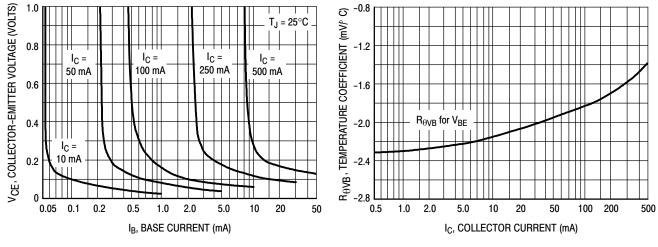
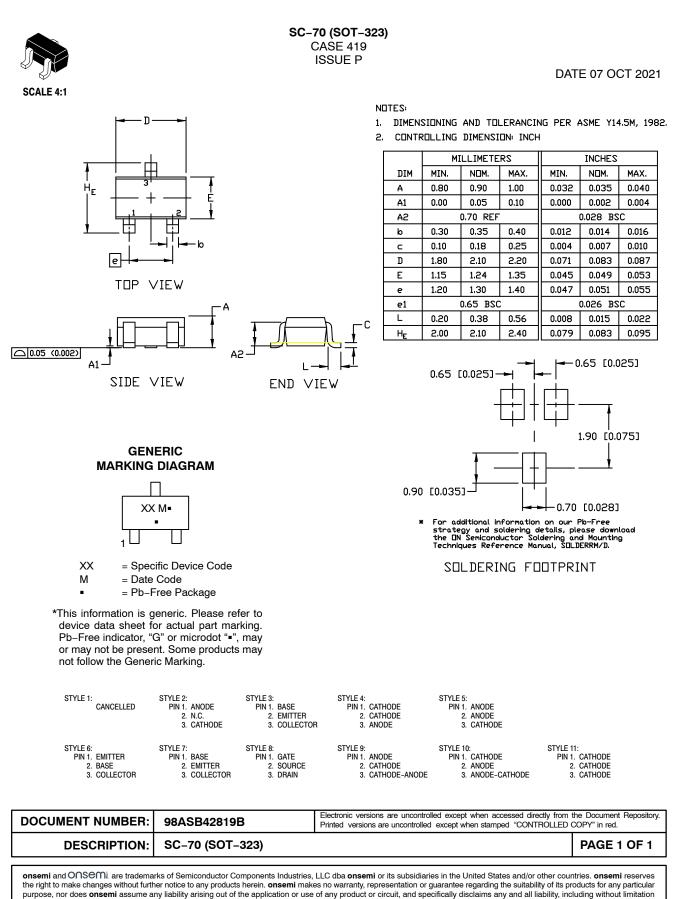


Figure 8. Collector Saturation Region

Figure 9. Base–Emitter Temperature Coefficient

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